

Summary

A semiconductor pressure sensor comprises a Silicon substrate (1) with the diaphragm(10) which produces a distortion depending on a pressure , strain gauges (5a, 5b, 5c, 5d) which are provided on the diaphragm (10) and is formed by diffusion resistors, a PN-junction area which is provided adjacent in the strain gauges (5a, 5b, 5c, 5d) and which the reverse bias is applied to.